




DOCUMENT CHANGE REQUEST

DCR number		1637		Changes required for: General		Originator: Steve Thacker	
Date: 2024/03/04				Date sent: 2024/02/05		Organisation: ESCC Executive Secretariat	
Status: IMPLEMENTED							
Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10						
Number:	5205/023		Issue:	9			
Other documents affected:							
Page:							
Various; see attached spec mark-up Draft 10 for details							
Paragraph:							
See below							
Original wording:							
As per spec issue 9							
Proposed wording:							
Amend the maximum limit for Gate-to-Source Threshold Voltage, VGS(th), as follows: see attached spec mark-up Draft 10A for details.							
Paras. 2.4.1, 2.5, 2.6, 2.10.2: to be 4.7V maximum (was 4.5V max.)							
Para. 2.4.2: for +125C only: to be 4.1V maximum (was 3.7V max.)							
Justification:							
This DCR is raised on behalf of Manufacturer STM.							
STM stated: The reason is: better limit definition due to old and poor statistical data							

Attachments:
escc5205023iss10_draft_a_in_review.docx
Modifications:
N/A
Approval signature:

Date signed:
2024-03-04